DMN3024LK3

30V TO252 (DPAK) N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}$	I_D T_A = 25°C
30V	24mΩ @ V_{GS}= 10V	14.4A
	39mΩ @ V_{GS}= 4.5V	11.6A

Features and Benefits

- Low on-resistance
- Fast switching speed
- Low gate drive
- "Green" component and RoHS compliant (Note 1)

Description and Applications

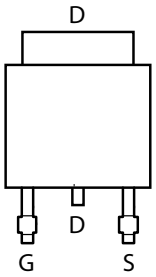
This new generation MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- DC-DC Converters
- Power management functions

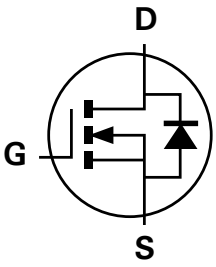
Mechanical Data

- Case: TO-252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0 (Note 1)
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals Connections: See Diagram
- Terminals: Matte Tin Finish annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Below
- Ordering Information: See Below
- Weight: 0.33 grams (approximate)

TOP VIEW



PIN OUT -TOP VIEW



Equivalent Circuit

Ordering Information (Note 1)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DMN3024LK3-13	N3024L	13	16	2,500

Note: 1. Diodes, Inc. defines "Green" products as those which are Eu RoHS compliant and contain no halogens or antimony compounds; further information about Diodes Inc.'s "Green" Policy can be found on our website. For packaging details, go to our website.

Marking Information

= Manufacturer's Marking
N3024L = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 09 = 2009)
WW = Week (01-52)

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Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic			Symbol	Value	Unit
Drain-Source voltage			V_{DSS}	30	V
Gate-Source voltage			V_{GS}	±20	V
Continuous Drain current	V_{GS} = 10V	(Note 3)	I_D	14.4	A
		T_A=70°C (Note 3)		12.0	
		(Note 2)		9.78	
Pulsed Drain current	V_{GS}= 10V	(Note 4)	I_{DM}	46.5	A
Continuous Source current (Body diode)		(Note 3)	I_S	12	A
Pulsed Source current (Body diode)		(Note 4)	I_{SM}	46.5	A

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Value	Unit
Power dissipation Linear derating factor	(Note 2)	P_D	4.1 32.5	W mW/°C
	(Note 3)		8.9 71.4	
	(Note 5)		2.17 17.4	
Thermal Resistance, Junction to Ambient	(Note 2)	$R_{\theta JA}$	30.8	°C/W
	(Note 3)		14.0	
	(Note 5)		57.6	
Thermal Resistance, Junction to Lead	(Note 6)	$R_{\theta JL}$	2.24	
Operating and storage temperature range		T_J, T_{STG}	-55 to 150	°C

Notes:
2. For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
3. Same as note 2, except the device is measured at t ≤ 10 sec.
4. Same as note 2, except the device is pulsed with D = 0.02 and pulse width 300 µs. The pulse current is limited by the maximum junction temperature.
5. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
6. Thermal resistance from junction to solder-point (at the end of the drain lead).

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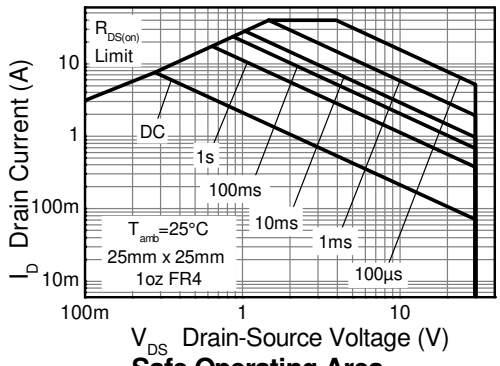
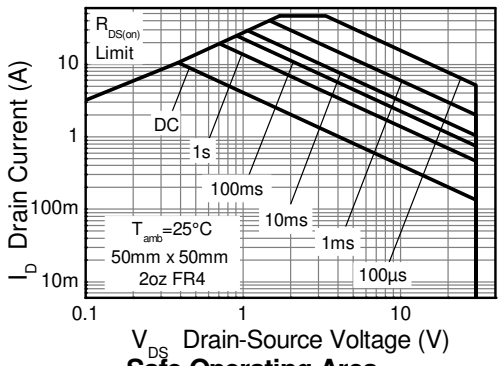
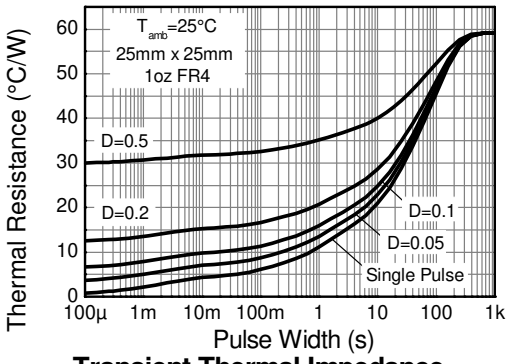
Thermal Characteristics



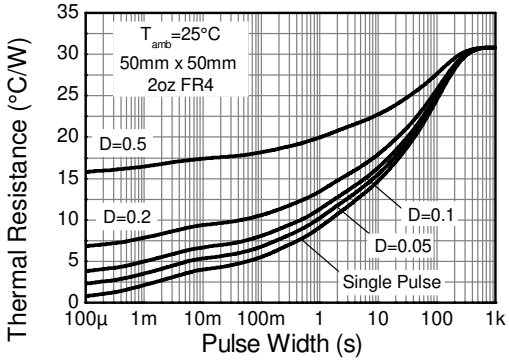
Safe Operating Area



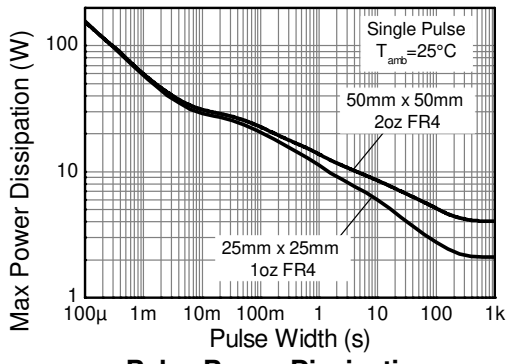
Safe Operating Area



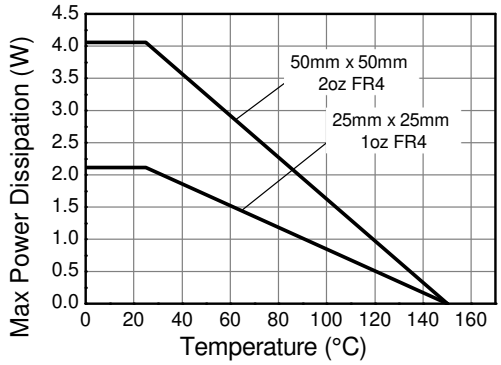
Transient Thermal Impedance



Transient Thermal Impedance



Pulse Power Dissipation



Derating Curve

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Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	30	—	—	V	I_D = 250μA, V_{GS}= 0V
Zero Gate Voltage Drain Current	I_{DSS}	—	—	0.5	μA	V_{DS}= 30V, V_{GS}= 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS}= ±20V, V_{DS}= 0V
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(th)}$	1.0	—	3.0	V	I_D= 250μA, V_{DS}= V_{GS}
Static Drain-Source On-Resistance (Note 7)	$R_{DS\ (ON)}$	—	—	0.024	Ω	V_{GS}= 10V, I_D= 7.0A
				0.039		V_{GS}= 4.5V, I_D= 6.0A
Forward Transconductance (Notes 7 & 8)	g_{fs}	—	16.5	—	S	V_{DS}= 15V, I_D= 7.0A
Diode Forward Voltage (Note 7)	V_{SD}	—	0.82	1.2	V	I_S= 1.7A, V_{GS}= 0V
Reverse recovery time (Note 8)	t_{rr}		12	—	ns	I_S= 2.2A, di/dt= 100A/μs
Reverse recovery charge (Note 8)	Q_{rr}	—	4.8	—	nC	
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	608	—	pF	V_{DS}= 15V, V_{GS}= 0V f= 1MHz
Output Capacitance	C_{oss}	—	132	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	71	—	pF	
Total Gate Charge	Q_g	—	12.9	—	nC	V_{DS}= 15V, V_{GS}= 10V I_D= 7A
Gate-Source Charge	Q_{gs}	—	2.5	—	nC	
Gate-Drain Charge	Q_{gd}	—	2.5	—	nC	
Turn-On Delay Time (Note 9)	$t_{D(on)}$	—	2.9	—	ns	V_{DD}= 15V, V_{GS}= 10V I_D= 1A, $R_G \cong 6.0\Omega$
Turn-On Rise Time (Note 9)	t_r	—	3.3	—	ns	
Turn-Off Delay Time (Note 9)	$t_{D(off)}$	—	16	—	ns	
Turn-Off Fall Time (Note 9)	t_f	—	8	—	ns	

Notes:
7. Measured under pulsed conditions. Pulse width ≤ 300μs; duty cycle ≤ 2%
8. For design aid only, not subject to production testing.
9. Switching characteristics are independent of operating junction temperatures.

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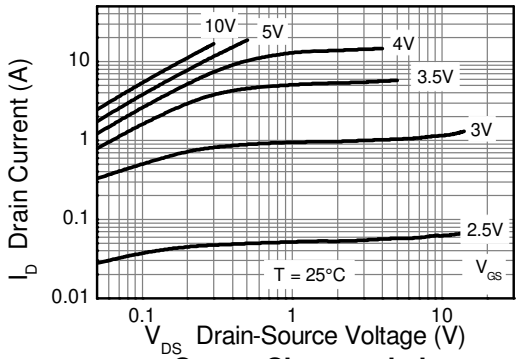
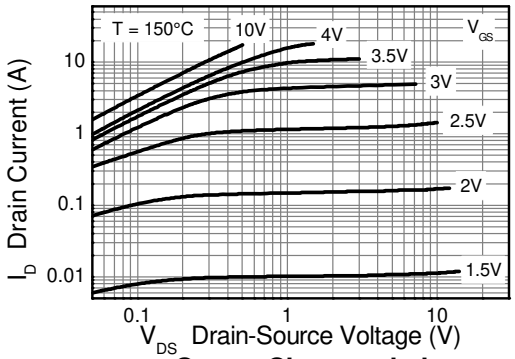
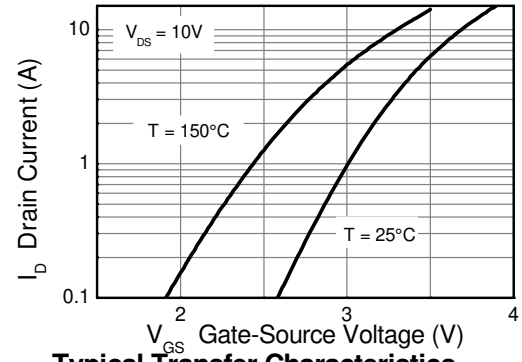
Typical Characteristics



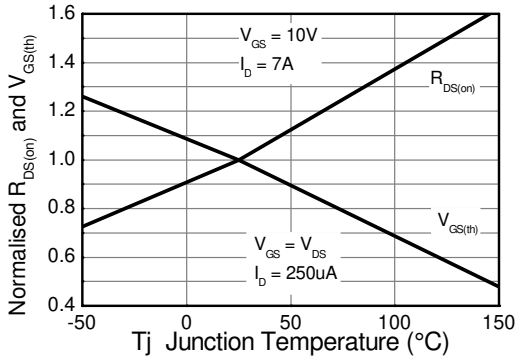
Output Characteristics



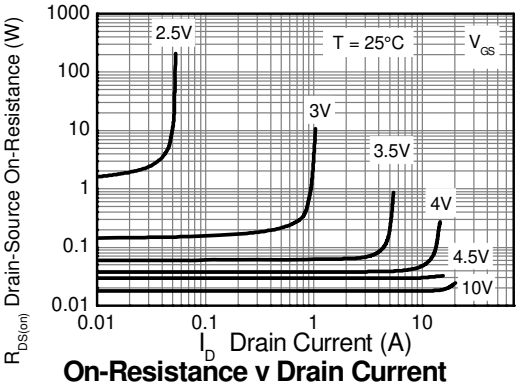
Output Characteristics



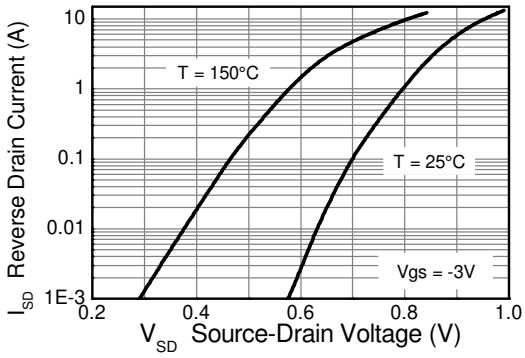
Typical Transfer Characteristics



Normalised Curves v Temperature



On-Resistance v Drain Current



Source-Drain Diode Forward Voltage

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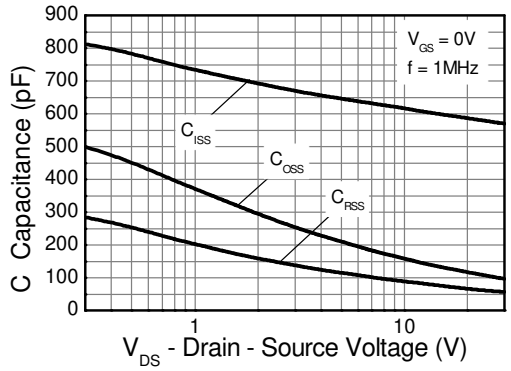
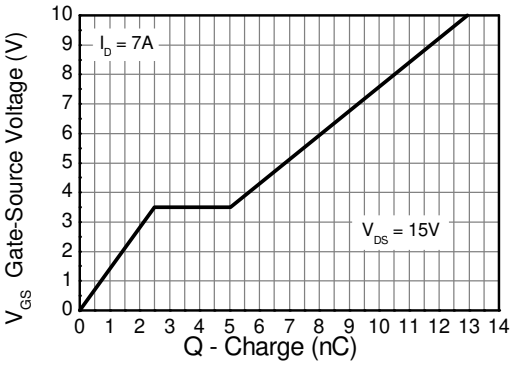
Typical Characteristics - continued

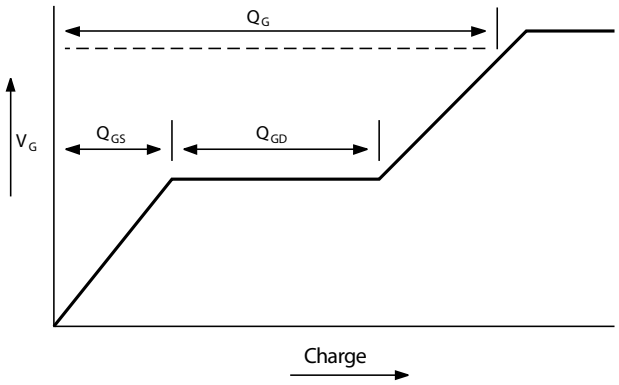


Capacitance v Drain-Source Voltage

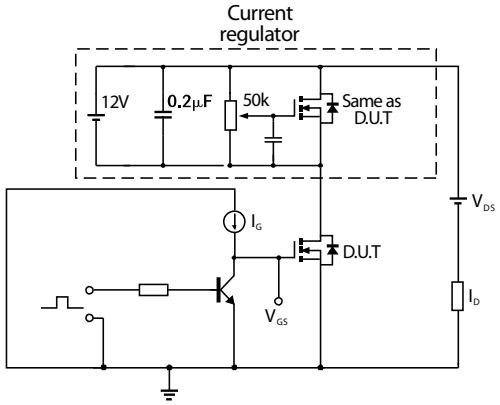


Gate-Source Voltage v Gate Charge

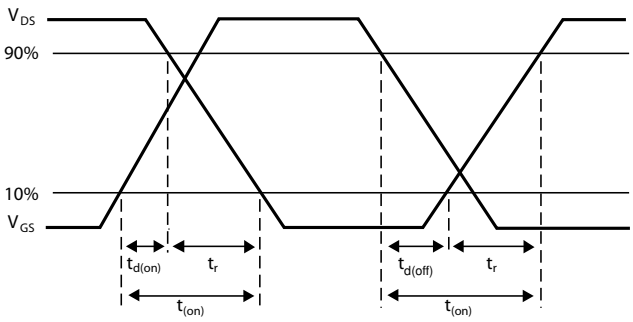
Test Circuits



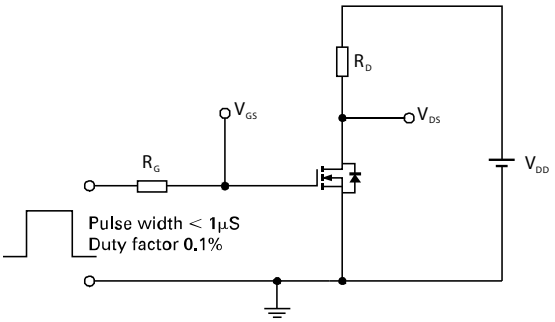
Basic gate charge waveform



Gate charge test circuit



Switching time waveforms



Switching time test circuit

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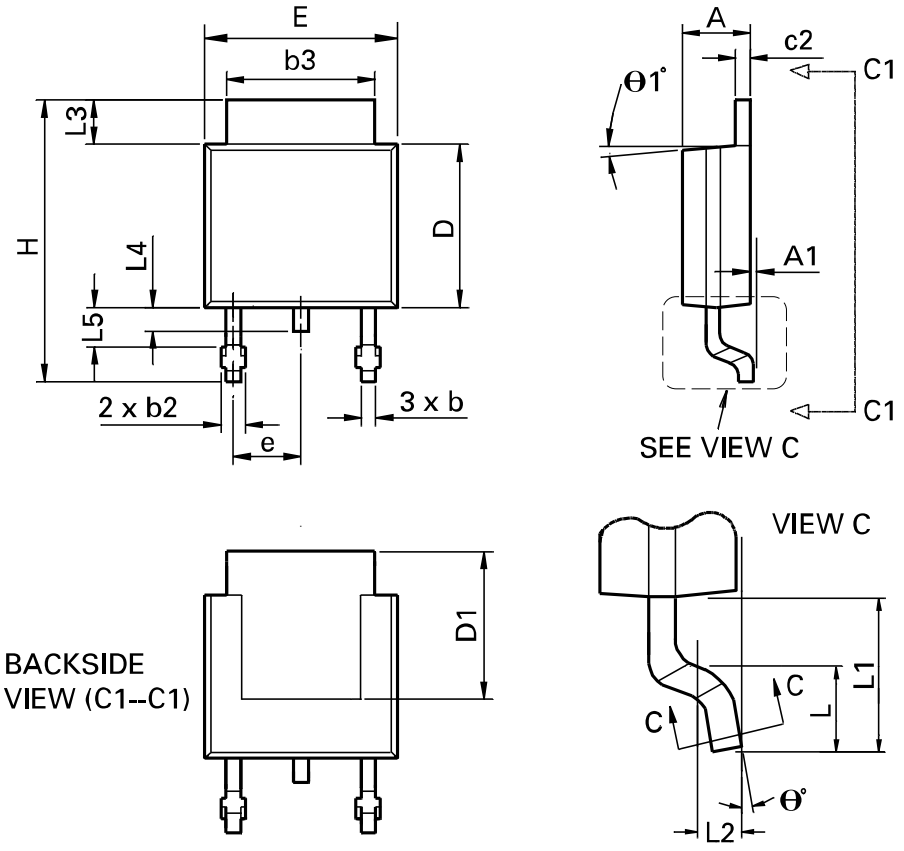
Package Outline Dimensions



DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min	Max	Min	Max		Min	Max	Min	Max
A	0.086	0.094	2.18	2.39	**e**	0.090 BSC		2.29 BSC	
A1	-	0.005	-	0.127	**H**	0.370	0.410	9.40	10.41
b	0.020	0.035	0.508	0.89	**L**	0.055	0.070	1.40	1.78
b2	0.030	0.045	0.762	1.14	**L1**	0.108 REF		2.74 REF	
b3	0.205	0.215	5.21	5.46	**L2**	0.020 BSC		0.508 BSC	
c	0.018	0.024	0.457	0.61	**L3**	0.035	0.065	0.89	1.65
c2	0.018	0.023	0.457	0.584	**L4**	0.025	0.040	0.635	1.016
D	0.213	0.245	5.41	6.22	**L5**	0.045	0.060	1.14	1.52
D1	0.205	-	5.21	-	**θ1°**	0°	10°	0°	10°
E	0.250	0.265	6.35	6.73	**θ°**	0°	15°	0°	15°
E1	0.170	-	4.32	-	-	-	-	-	-

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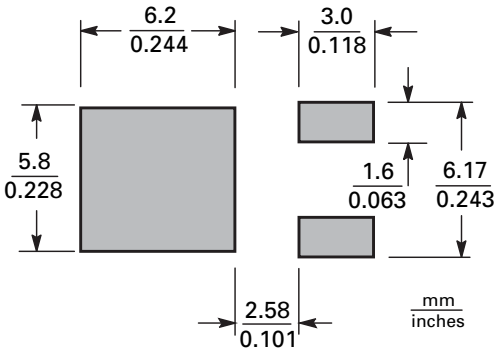
Suggested Pad Layout



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